



A 6.1 nW Wake-Up Receiver Achieving -80.5 dBm Sensitivity via a Passive Pseudo-Balun Envelope Detector



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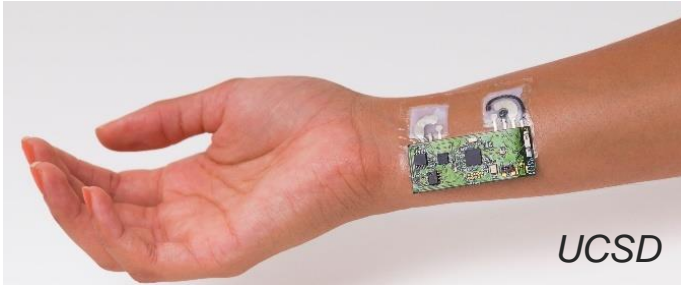


Motivation – Low-Power Wide-Area Networks (LPWAN)

Wearables/Medical

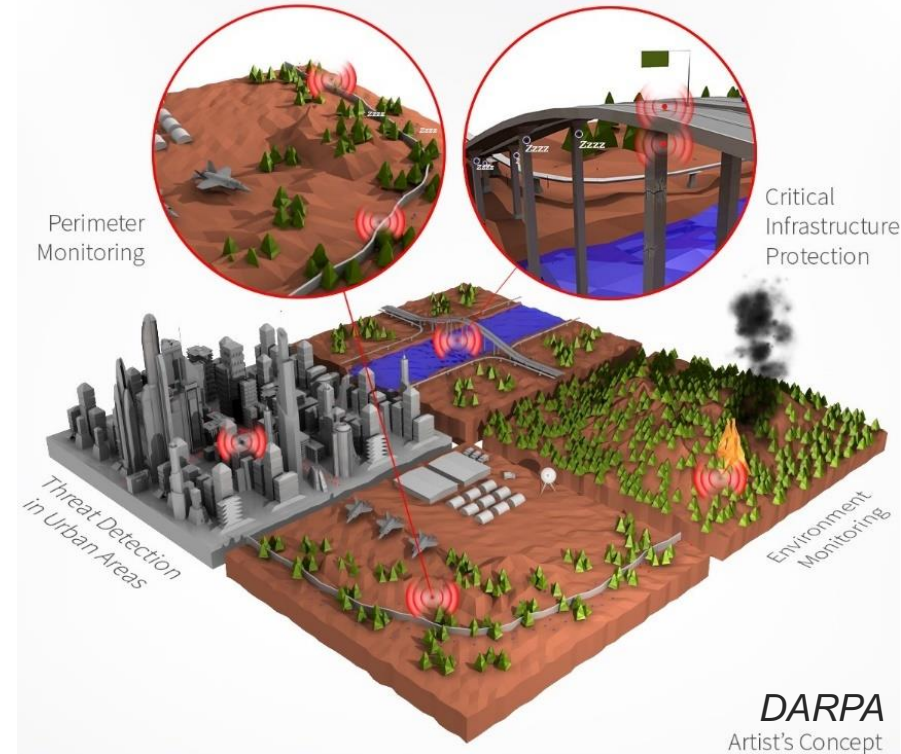


HTC



UCSD

Unattended ground sensors



Smart Meters



The age of Internet of Everything (IoE)

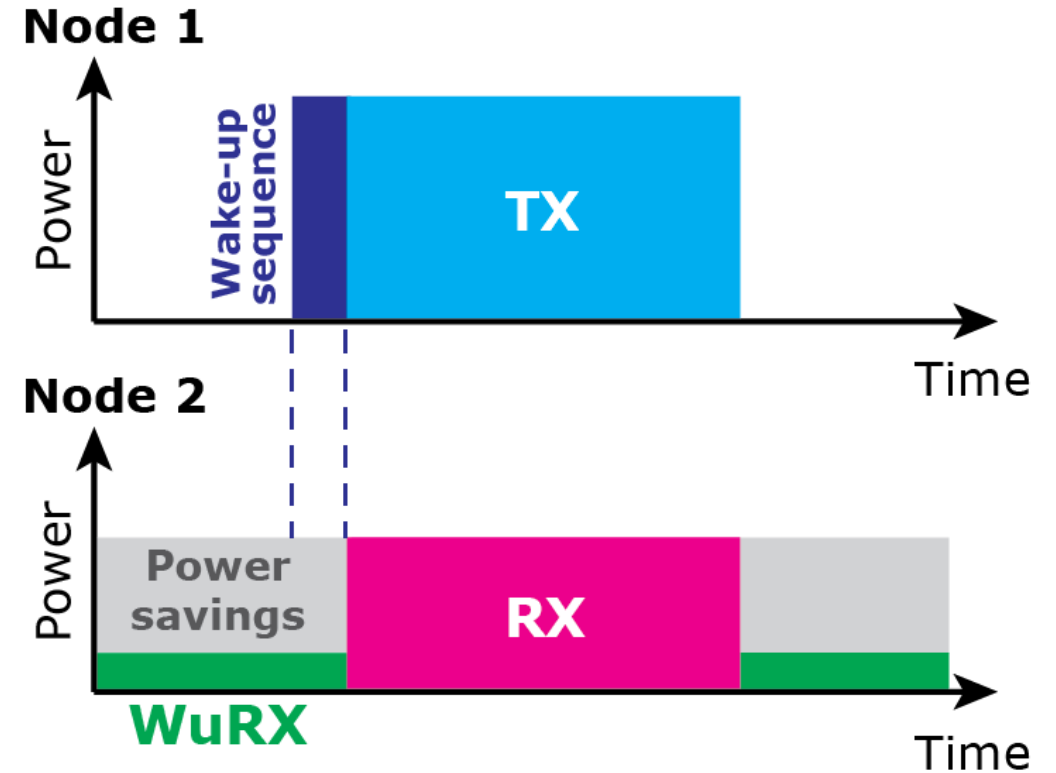
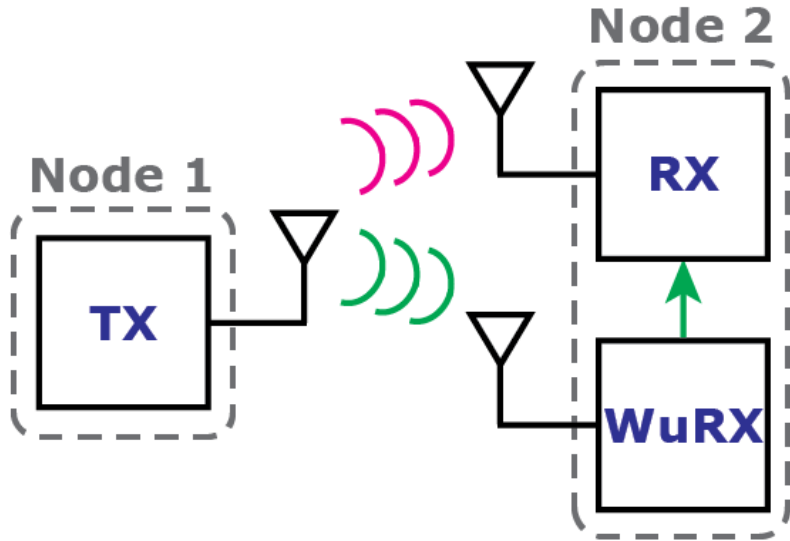
- 500 billion connected devices before 2030 [Cisco, 2014]

Event-driven applications focuses on lifetime and range

- Low power and high sensitivity are the main targets



Wake-up Receiver (WuRX)

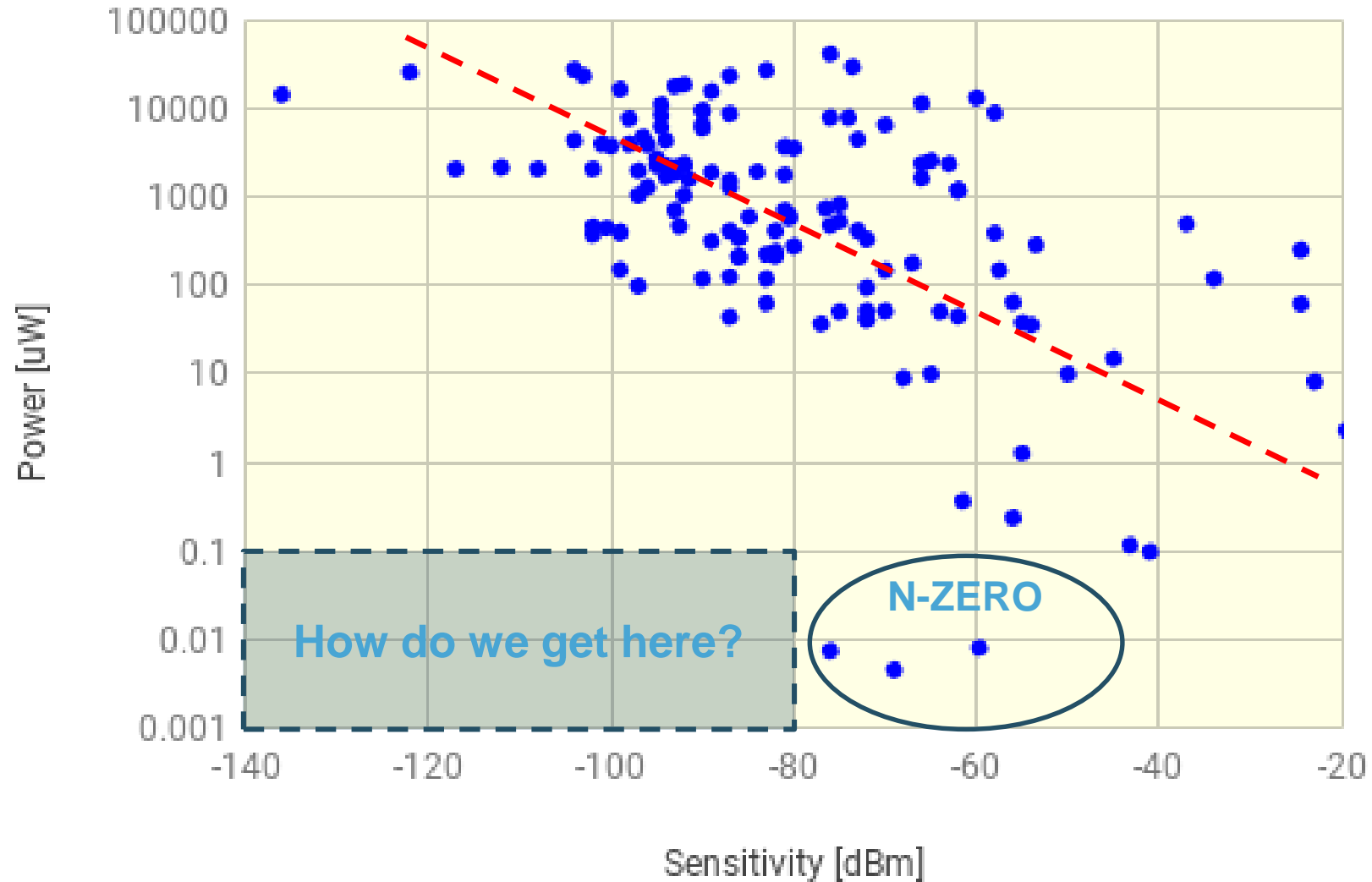


For infrequent event-driven networks:

- Always-ON WuRX extends the system lifetime
- WuRX sensitivity should be comparable with the main RX

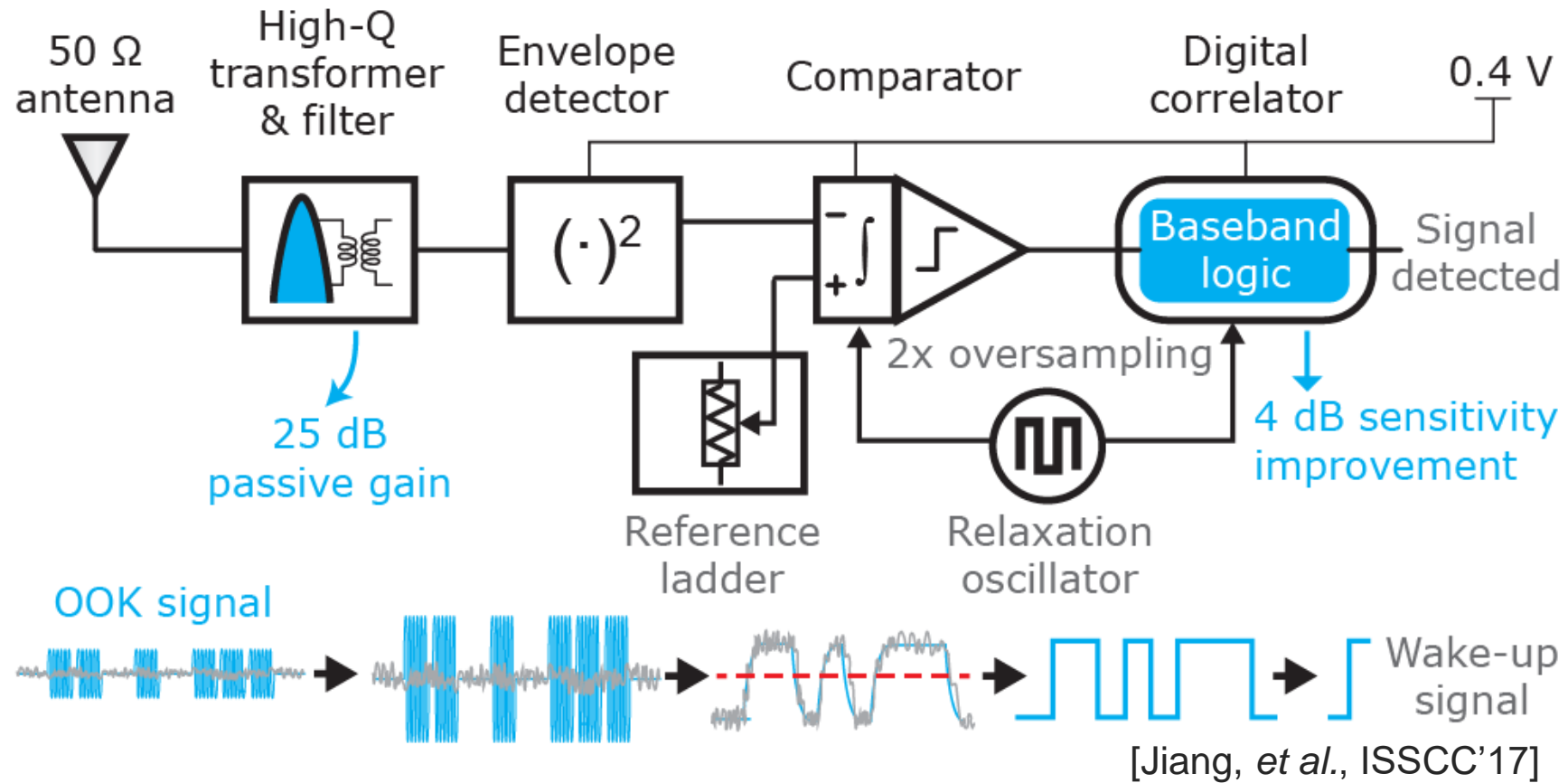


The Current State-of-the-Art





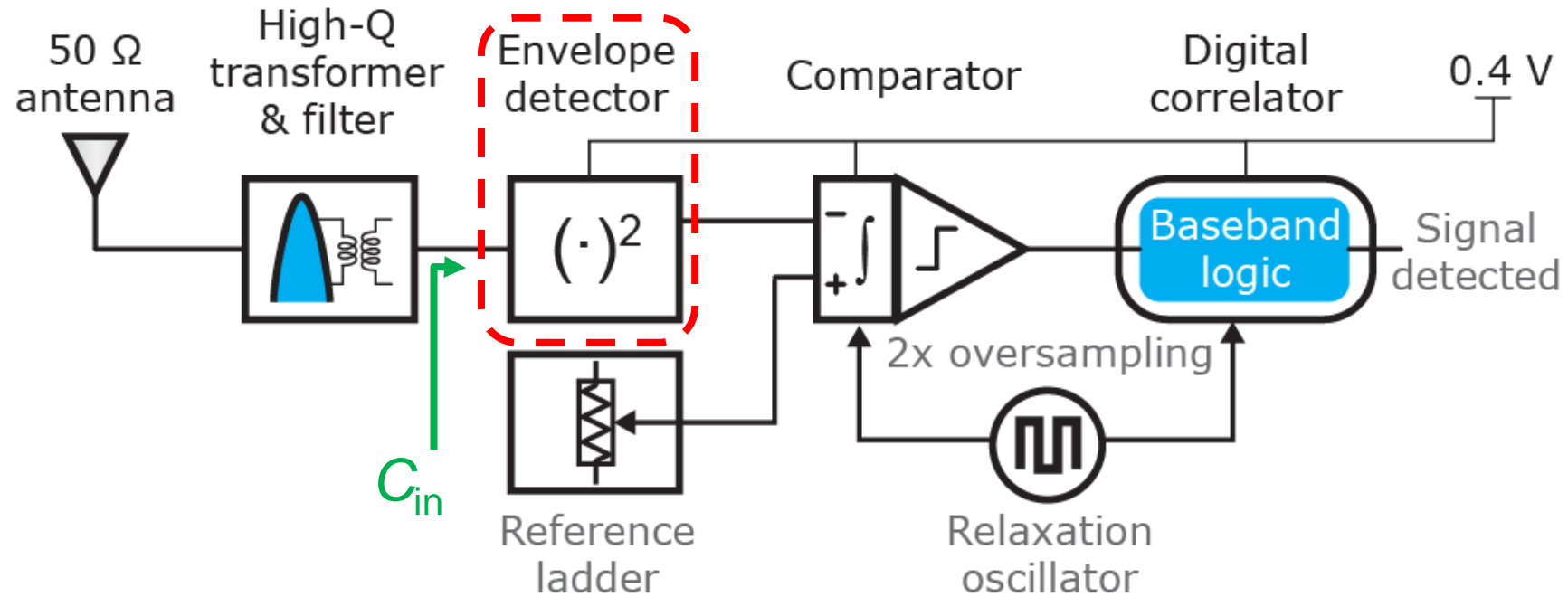
Direct ED nW WuRX Architecture



The combination of passive RF gain and a Direct ED architecture enables nW level WuRXs



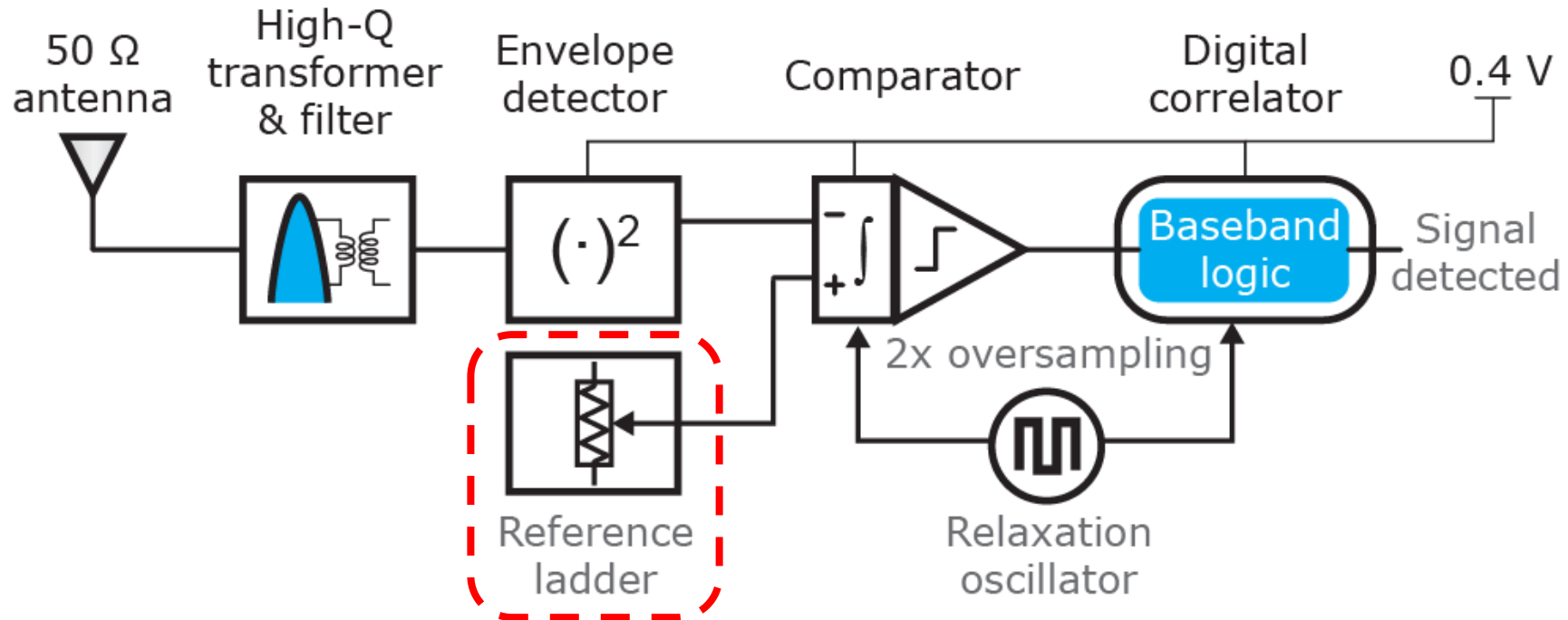
Problem 1: High Input Capacitance ED



High C_{in} ED limits carrier frequency and passive gain



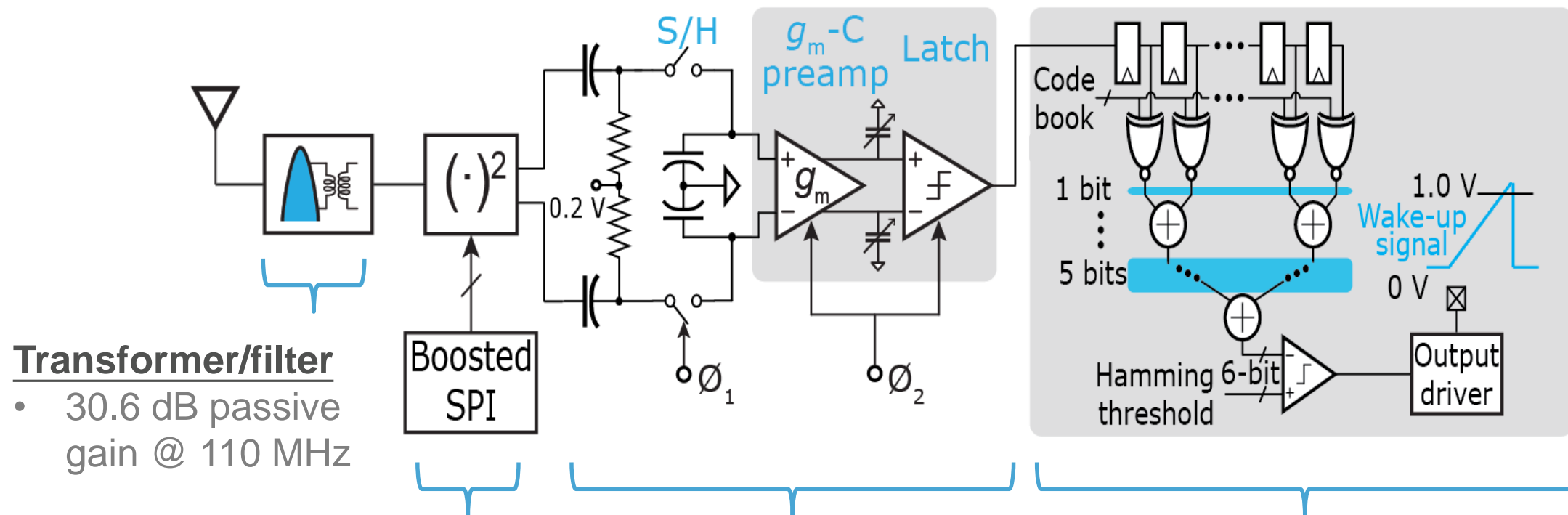
Problem 2: Single-ended Output ED



- Needs extra reference circuit for comparator
 - Extra tuning required for DC variation from PVT
 - Reference circuit is an additional noise source
- Could we eliminate the need for a reference circuit?



Proposed WuRX Architecture



Active pseudo-balun ED

- Single-ended input to pseudo-differential output
- Boosted SPI for super cut-off switches

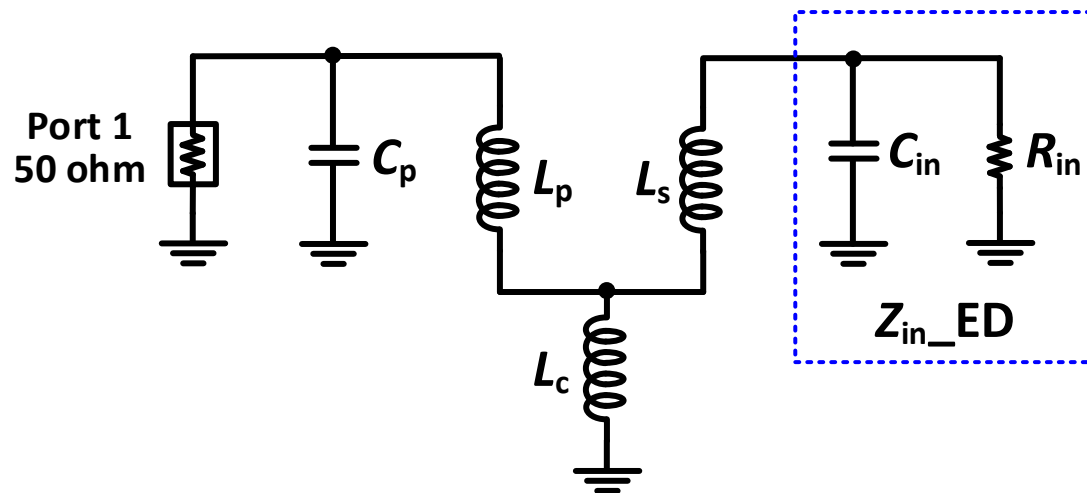
S/H stage and comparator

- S/H stage to handle asymmetric comparator kickback during ϕ_2

Digital correlator

- $6\times$ oversampling to overcome clock asynchronization and average low frequency noise
- 2.5 dB coding gain

110 MHz Transformer



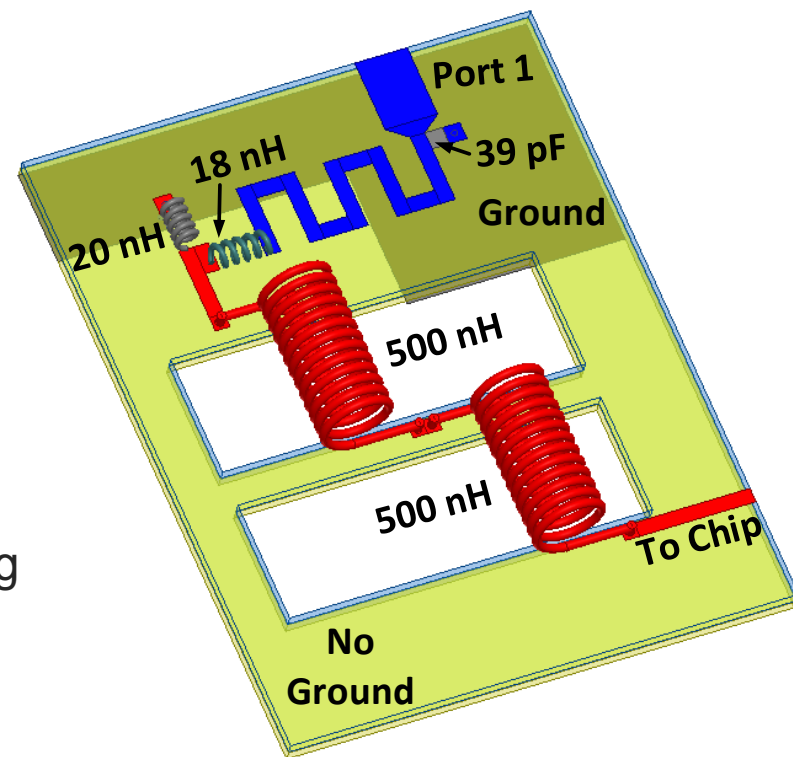
Transformer Structure

- Two stage LC to realize impedance transformation as well as filtering
- L_c is used to control the bandwidth and input matching

$$Gain_{\max} = \sqrt{R_L/R_S}$$

$$R_L = R_P || R_{in} = Q\omega L_S || R_{in}$$

- To achieve high gain, L_s and Q should be large
- To get large L_s , no additional cap is used in the secondary stage
- To get large Q , the inductor underneath the ground and substrate were removed

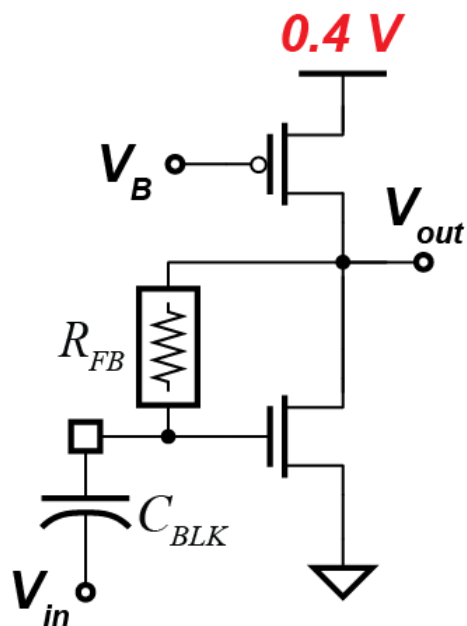


Transformer 3-D Model



Active vs. Passive ED (w/ the same BW)

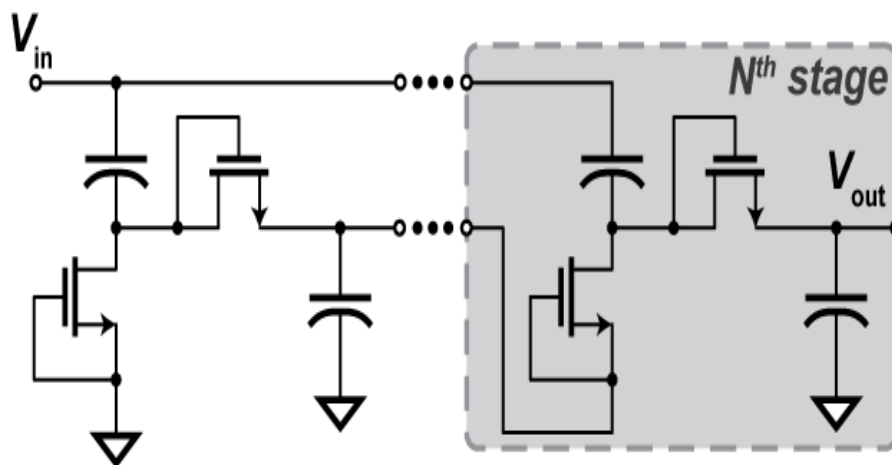
Active ED



Pros: high R_{in}
high conversion gain

Cons: high C_{in}
low SNR
non-zero power

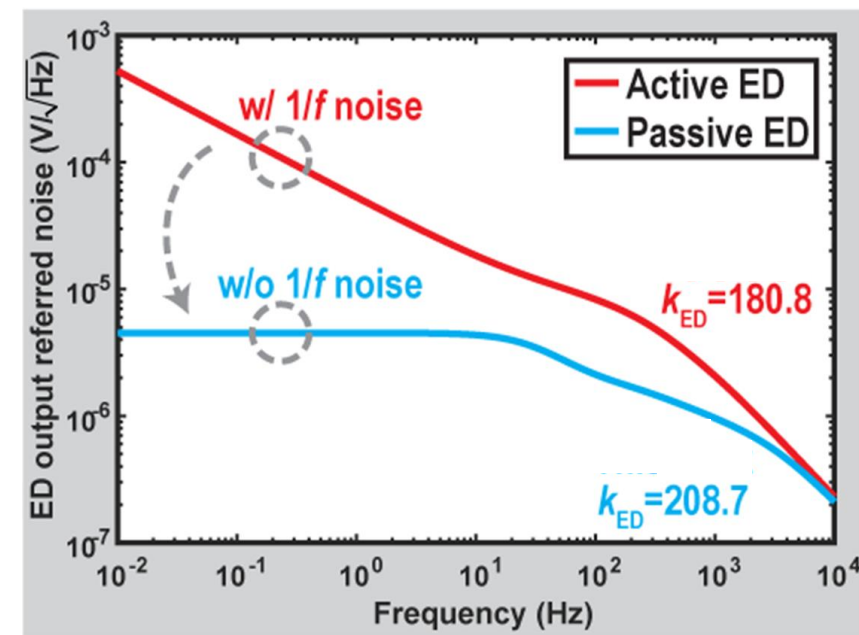
Passive ED



Pros: low C_{in}
high SNR
zero power

Cons: low R_{in}
low conversion gain

SNR

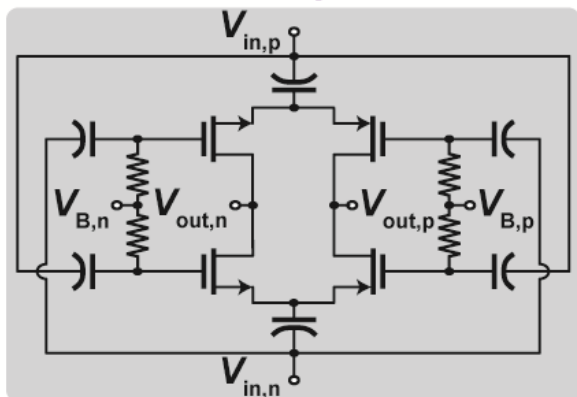


Passive ED has no $1/f$ noise
compared to active ED



Proposed Passive Pseudo-balun ED

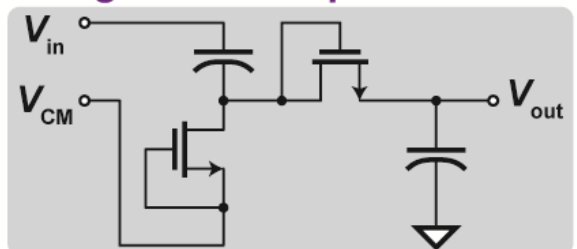
Differential input unit cell



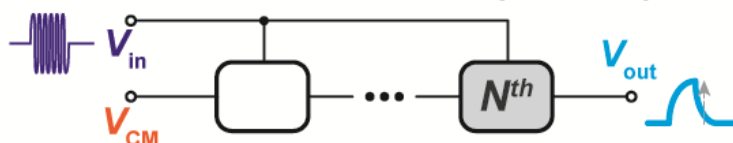
Problem 1: extra loading @ RF for biasing

Problem 2: differential input requires center-tapped transformer \rightarrow low Q ; low passive voltage gain

Single-ended input unit cell

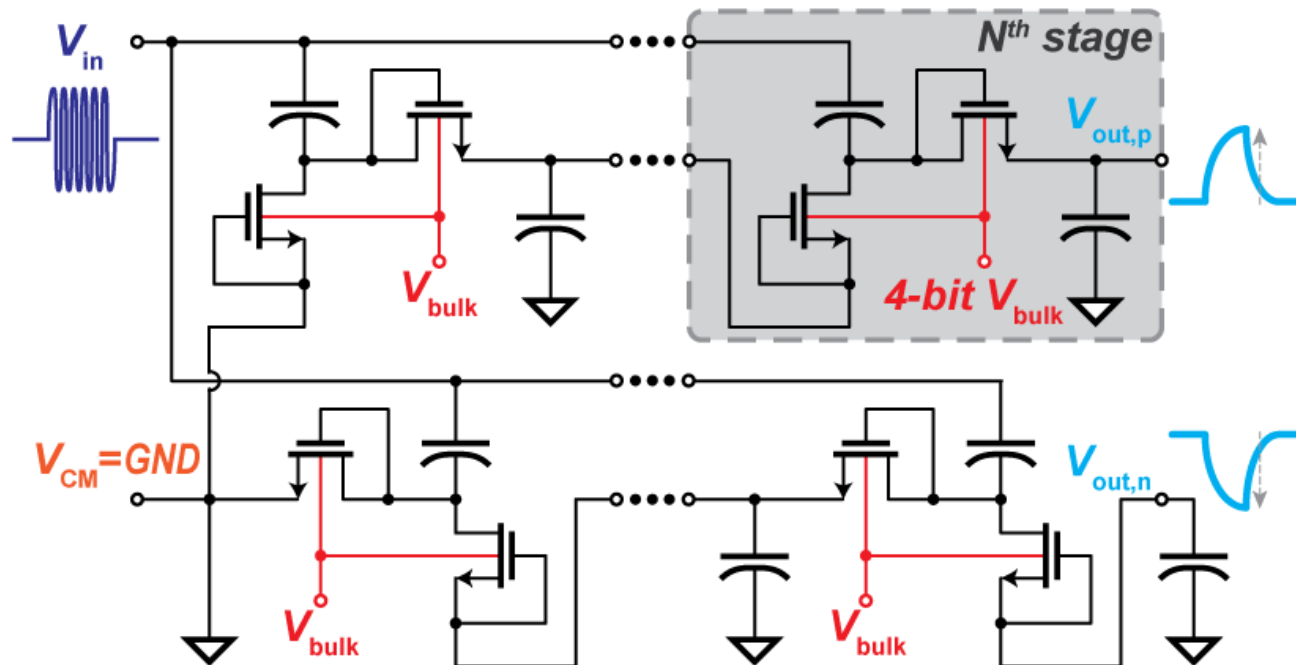


Problem 1: no transistor tuning capability



Problem 2: single-ended output ED requires extra reference circuit with tuning for comparator

Proposed ED



Pseudo-balun ED

Benefit 1: 2X conversion gain w/o output bandwidth penalty

Benefit 2: 1.5 dB sensitivity improvement vs. single branch only

Bulk tuning unit cell

Benefit 1: tunable V_t for PVT or sizing for lower C_{in}

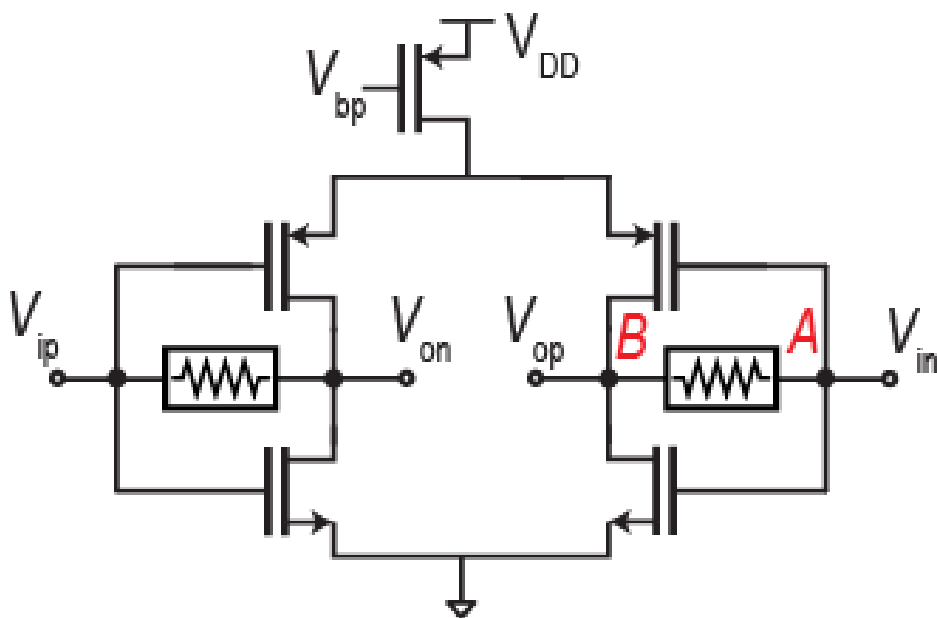
Benefit 2: no extra loading @ RF for biasing network



Baseband Amplifier

Design requirements:

- High input impedance to not degrade the ED gain & bandwidth
- High noise efficiency



2x current reuse reduces noise by 2x

Potential issue

- $Z_{in} = \frac{R}{A_V + 1} \parallel (A_V + 1)(C_{gd,n} + C_{gd,p})$
- Low R_{in} and high C_{in} due to Miller effect

Solutions:

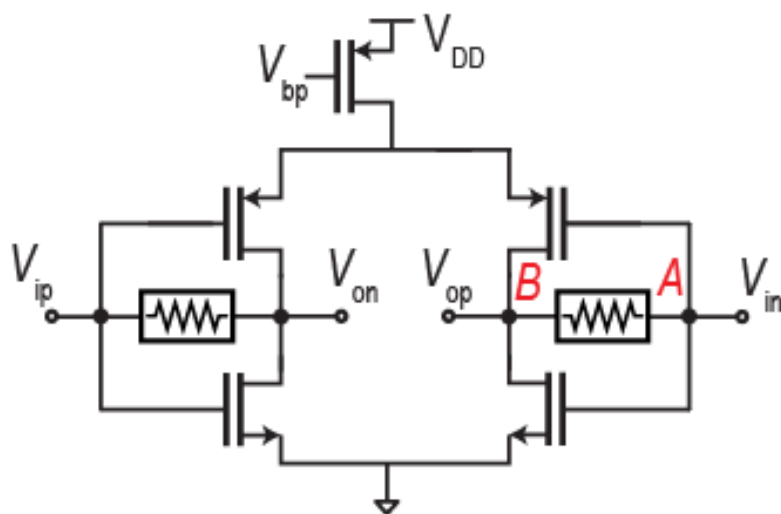
- Pseudo-resistor $> 1T\Omega$
- Neutralization capacitors cancel Miller capacitance

Achieves $9\mu V_{RMS}$ noise and an input impedance of $30G\Omega \parallel 0.4pF$ with only 3.4nW

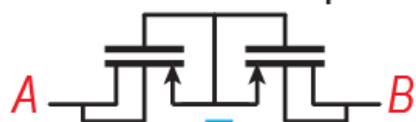


Baseband Amplifier

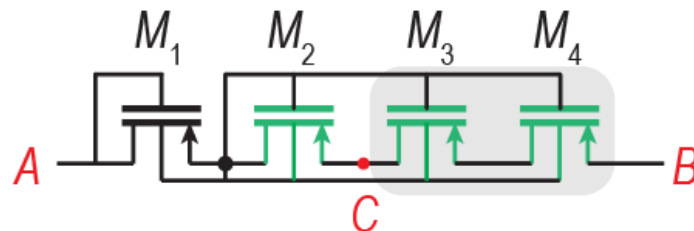
Current-reuse amplifier:



Conventional pseudo-resistor:

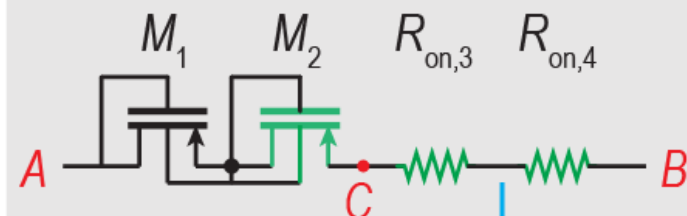


Fast start-up pseudo-resistor:

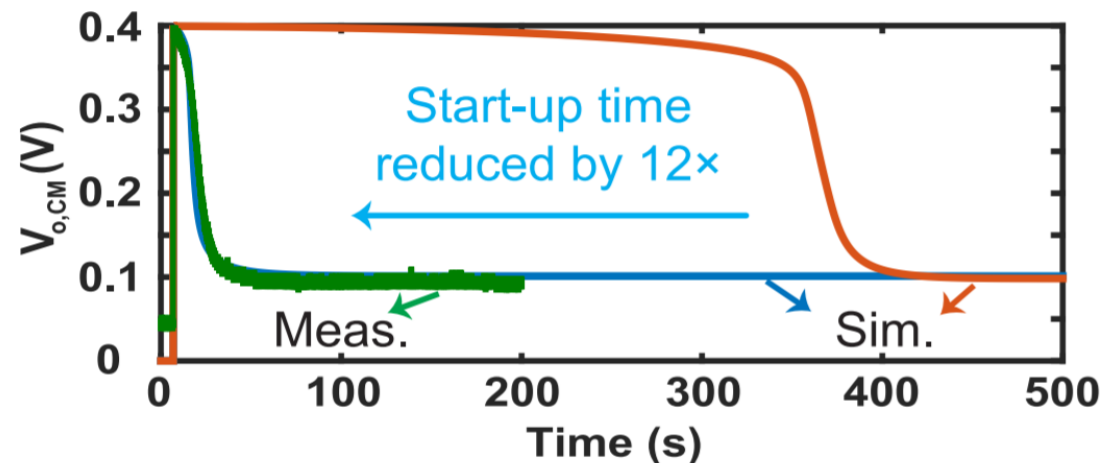
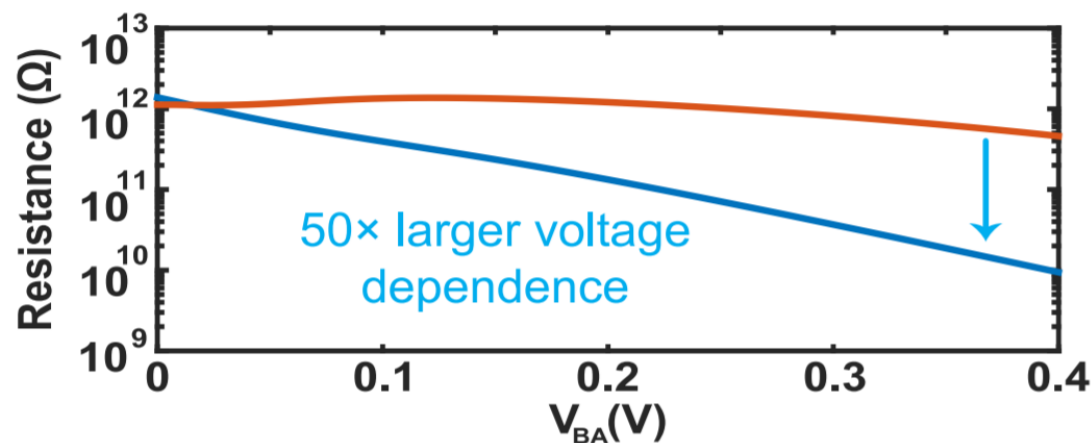


>400s)!

$V_{AC} \gg V_{CB} \approx 0$ during start-up:



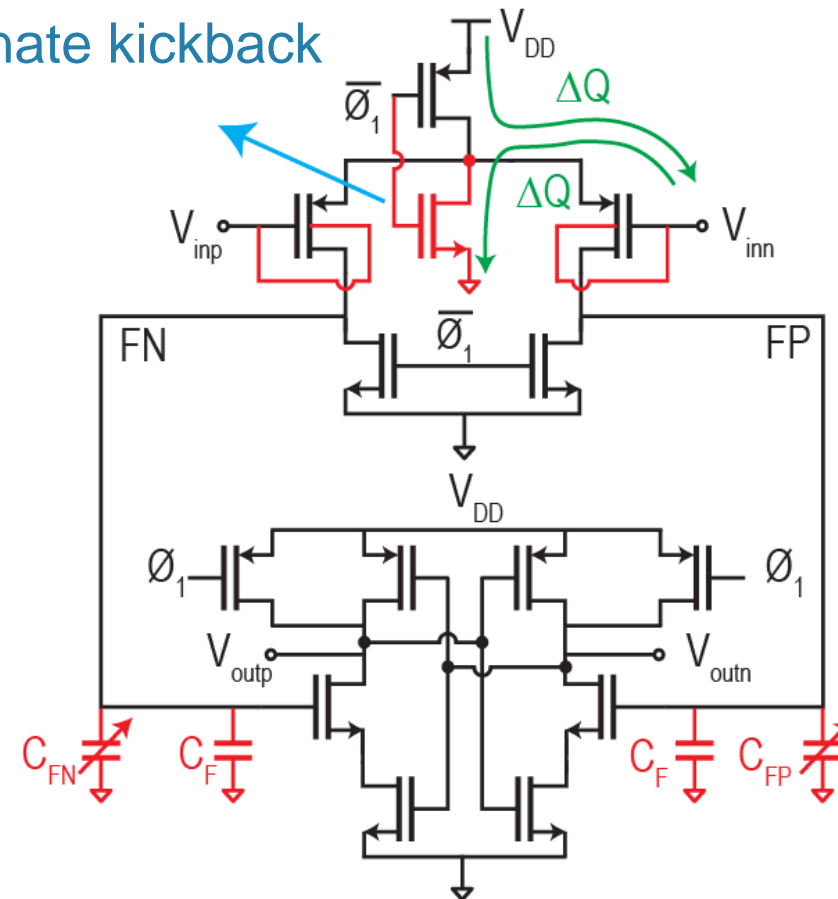
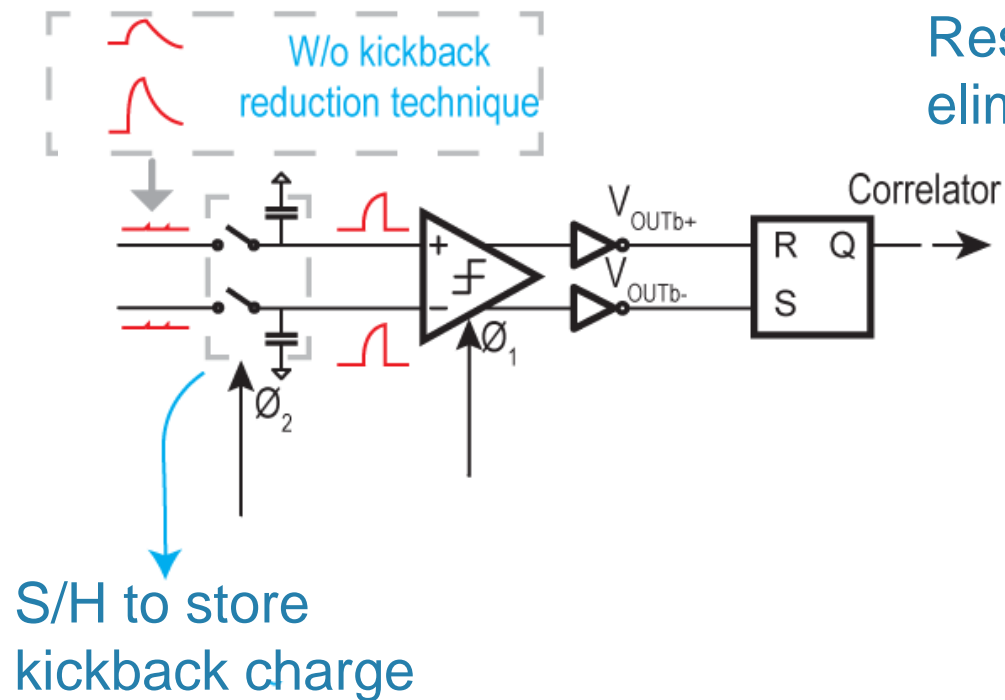
Subthreshold triode w/ reduced V_t during start-up \rightarrow low R_{on}



Utilizing asymmetric nonlinearity achieves 12× faster stat-up w/o compromising R_{in}



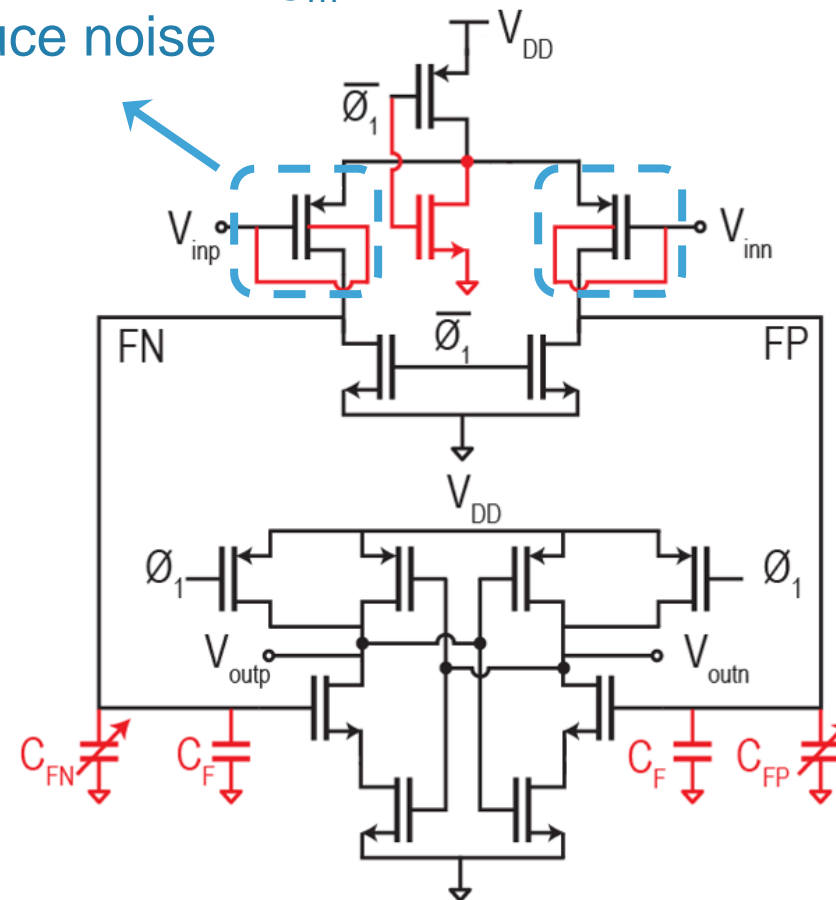
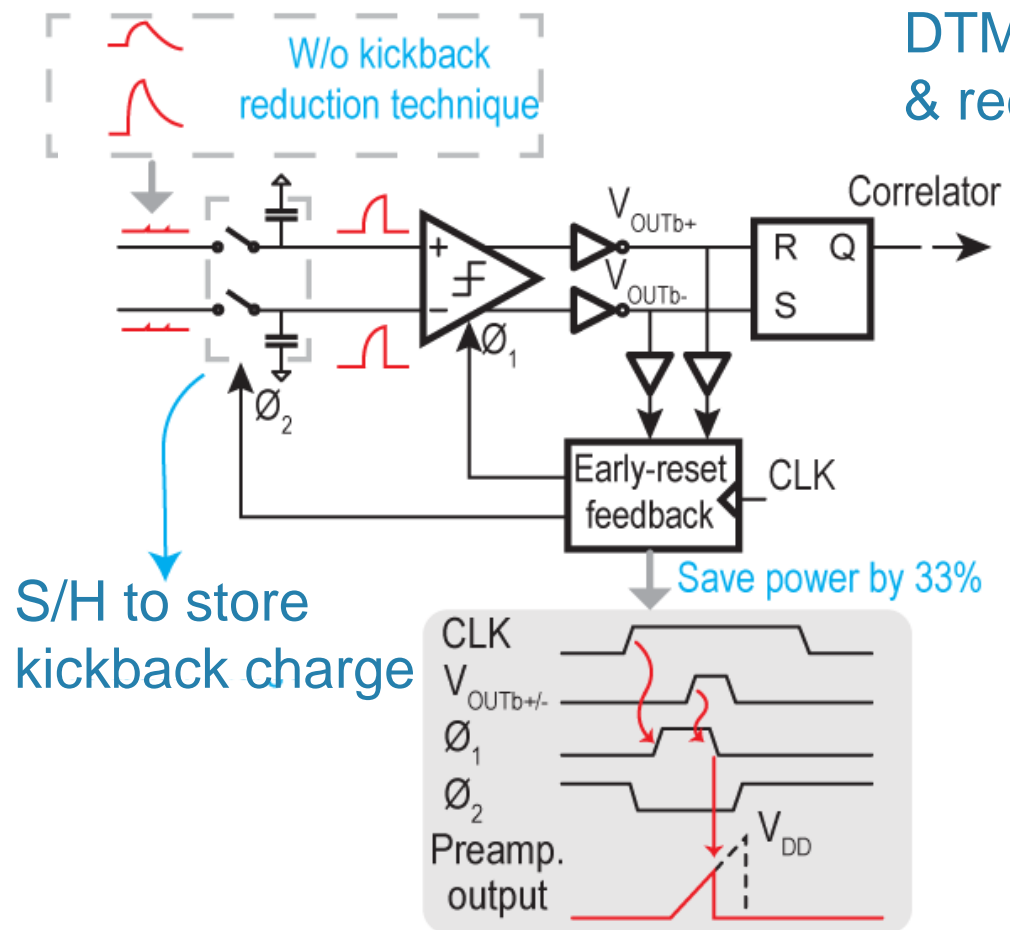
Comparator



S&H: balanced impedances & stores kickback charge temporarily
Reset transistor: Purge kickback charge before next cycle



Comparator

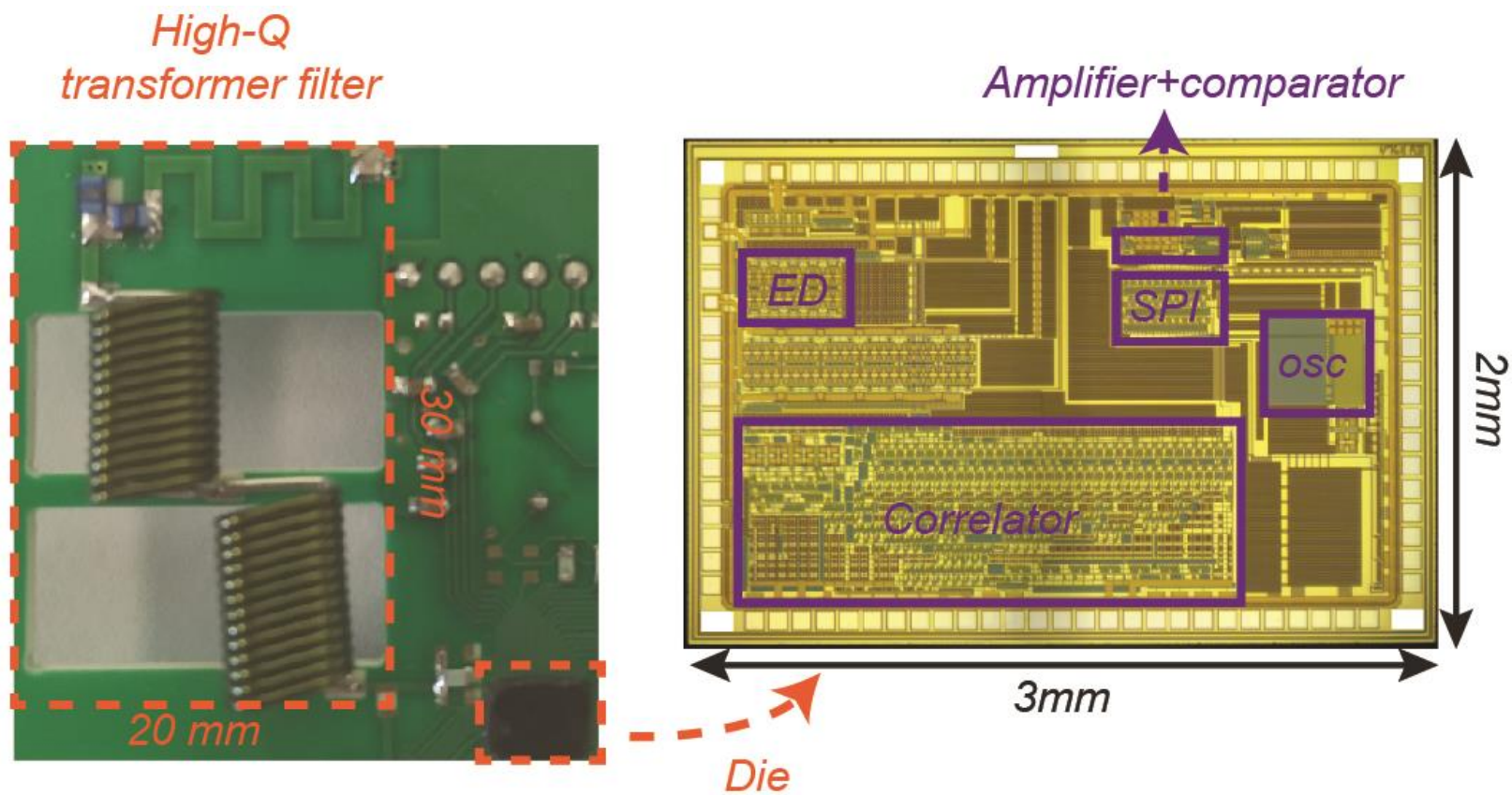


Early-reset: save dynamic power & generate non-overlapping clock





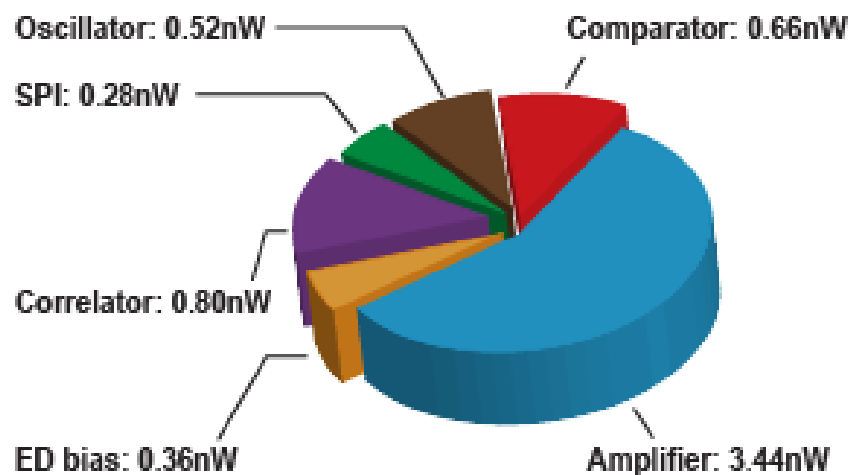
Board and die photo



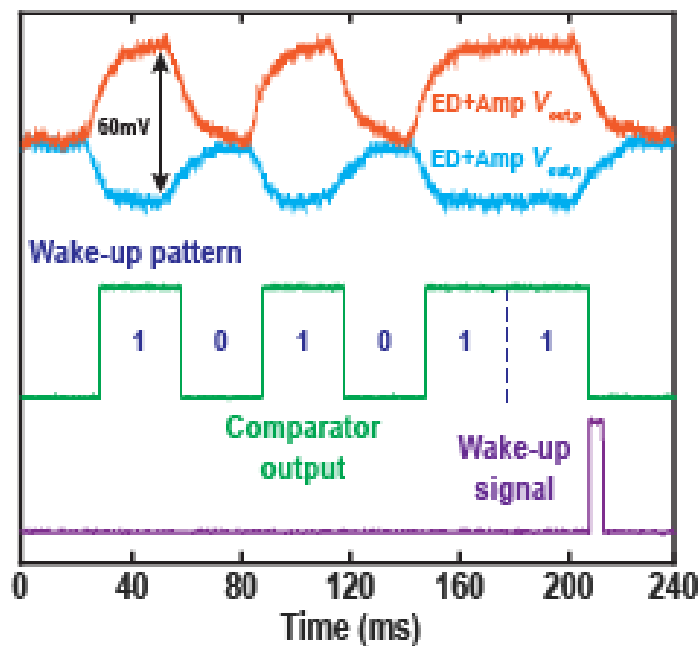


Measurement Results

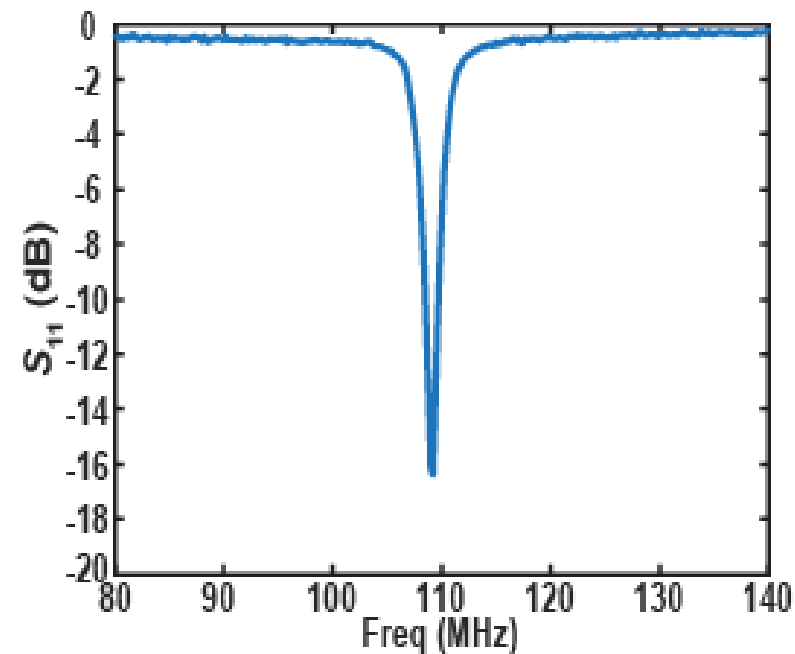
Power Breakdown



Transient Response



Input Matching

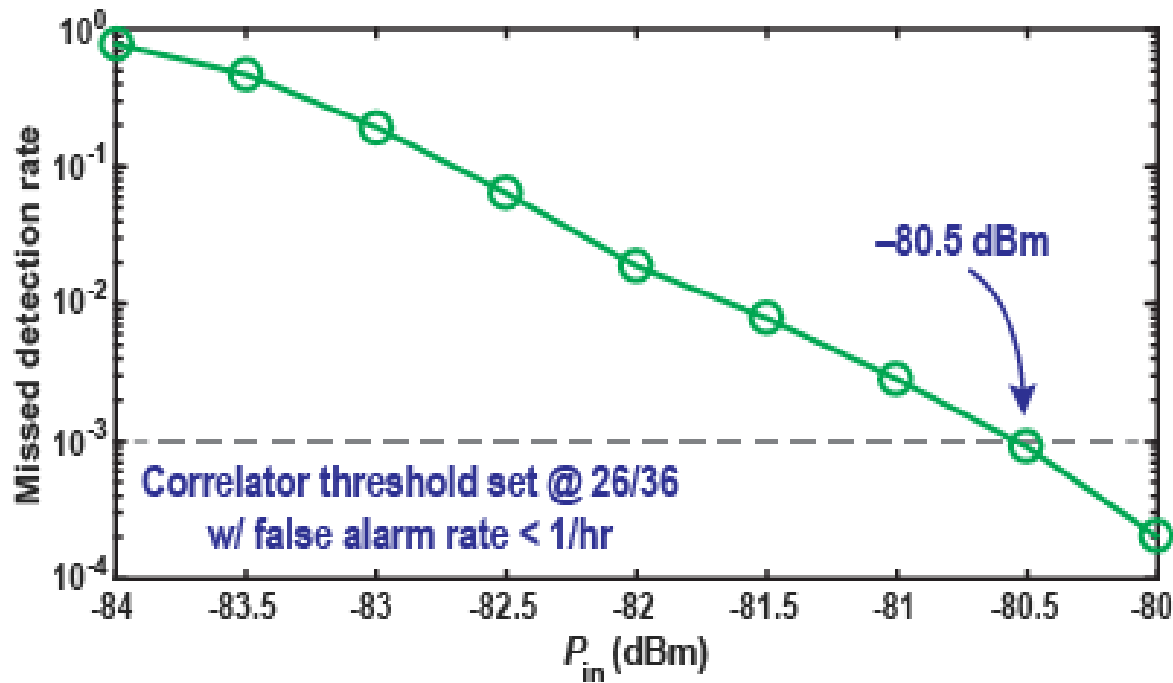


6.1 nW power consumption WuRX – Less than the leakage of a coin cell battery!

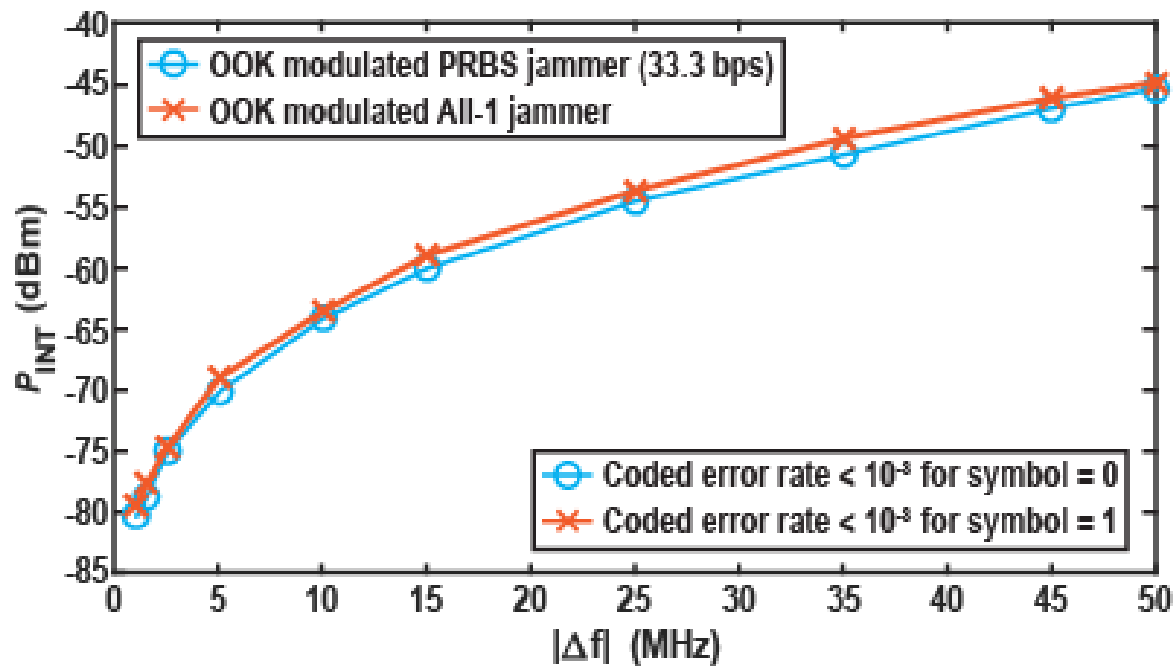


Measurement Results

Missed Detection Rate



Interference Sensitivity





Comparison to the State-of-the-Art

	[1] CICC'13	[4] CICC'17	[7] ESSCIRC'17	[8] ISSCC'18	[2] ISSCC'17	[5] ISSCC'18	This Work
Technology	130 nm	130 nm	180 nm	65 nm	180 nm	130 nm	180 nm
Supply Voltage	1.2 / 0.5 V	0.5 V	0.4 V	0.5 V	0.4 V	1.0 / 0.6 V	0.4 V
Digital Correlator	31-bit	11-bit [*]	32-bit	3~10-bit	32-bit	8-bit	36-bit[‡]
Clock	XTAL osc.	No	Relaxation osc.	Relaxation osc.	Relaxation osc.	Ring osc.	Relaxation osc.
Passive RF Voltage Gain	5 dB	27 dB [◁]	18.5 dB	N.R. [◇]	25 dB	27 dB	30.6 dB
Demodulator Type	Passive Dickson single-ended ED	Passive self-mixer	Active CG pseudo-balun ED	Active CS-CG single-ended ED	Active CS single-ended ED	Passive Dickson single-ended ED	Passive Dickson pseudo-balun ED
Carrier Frequency	403 MHz	550 MHz	405 MHz	57 kHz	113.5 MHz	151.8 MHz	109 MHz
Data Rate	12.5 kbps	400 kbps [†]	300 bps	336 bps	300 bps	200 bps	33.3 bps
Wake-Up Latency	2.48 ms	27.5 μ s	53.3 ms	8.9~29.8 ms	53.3 ms	>80 ms [▷]	180 ms
Sensitivity	−45 dBm	−56.4 dBm	−63.8 dBm	−60.1 dBm [‡]	−69 dBm	−76 dBm	−80.5 dBm
Sensitivity Normalized to 1/Latency[◦]	−58 dB	−79.2 dB	−70.2 dB	−68.5 dB [‡]	−75.4 dB	−81.5 dB	−84.2 dB
Power Consumption	116 nW	222 nW	4.5 nW	8 nW	4.5 nW	7.6 nW	6.1 nW

State-of-the-art performance: the highest sensitivity and the best sensitivity normalized to latency



Conclusion

- For event-driven applications with low-average throughput, WuRXs extend system lifetime
 - Design targets: Low power and high sensitivity
- The proposed design accomplishes this using:
 - Passive gain at RF with a high Q impedance transformer
 - Passive pseudo-balun ED with low C_{in}
 - A current-reuse baseband amplifier and two-stage integrating comparator
 - A low-power digital correlator with 6x oversampling
- **Result:** A 110 MHz, 6.1 nW, -80.5 dBm sensitivity WuRX



Acknowledgment

- This work is supported by the Defense Advanced Research Projects Agency (DARPA) under contract No. HR0011-15-C-0134
- Mentor Graphics for the use of Analog FastSPICE tool (AFS)

STUDENTS



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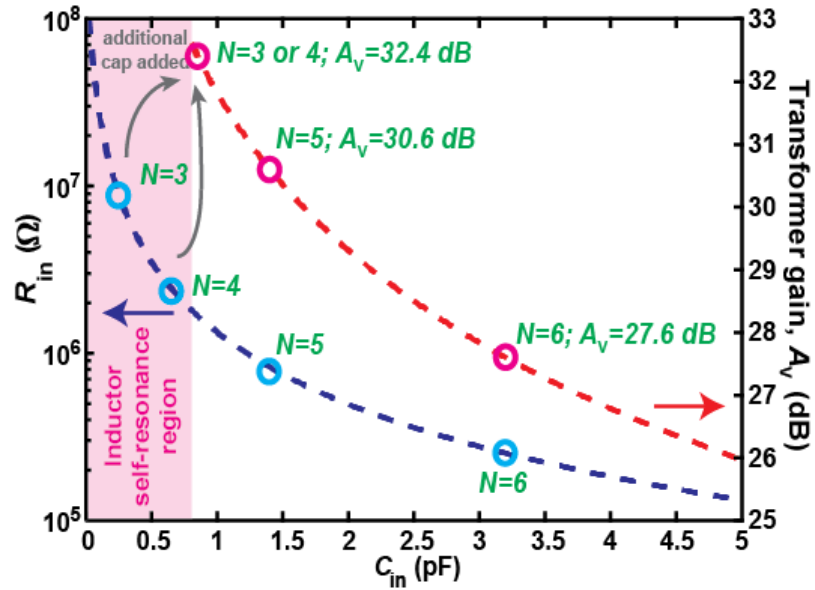


Backup

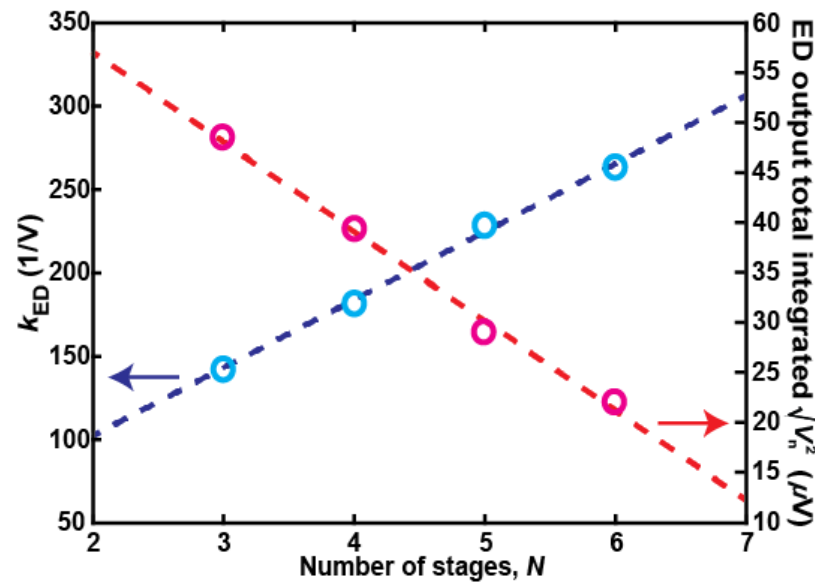


Passive ED Stage Optimization

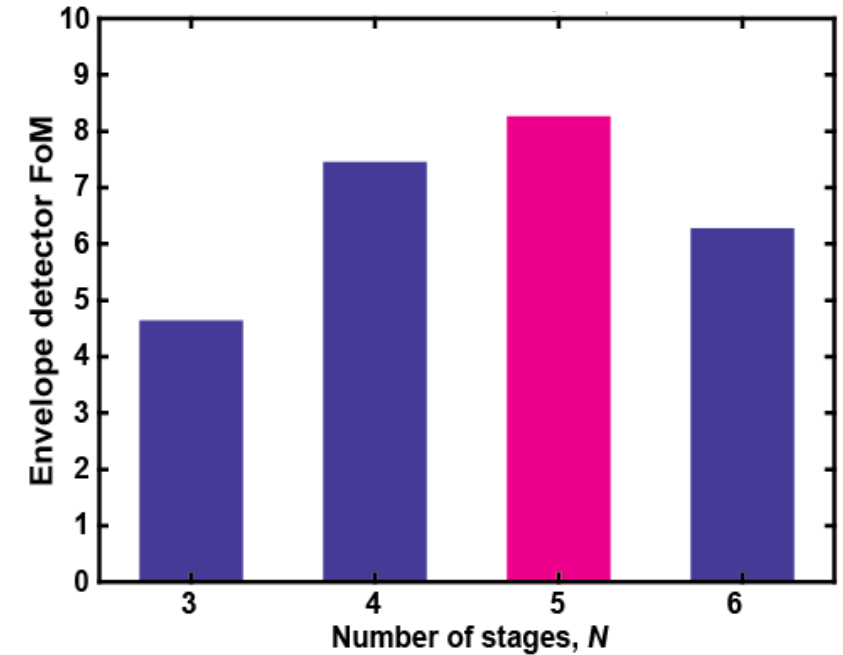
Transformer gain
for different N



k_{ED} and noise
for different N



$$SNR_{ED, norm} = \frac{A_v^2 \cdot k_{ED}}{\sqrt{V_n^2}} \cdot 10^{-9}$$



$N=5$ ED achieves the best SNR



The State-of-the-Art Landscape (Revised)

